

NPN 7 GHz wideband transistor

BFG591

FEATURES

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability.

APPLICATIONS

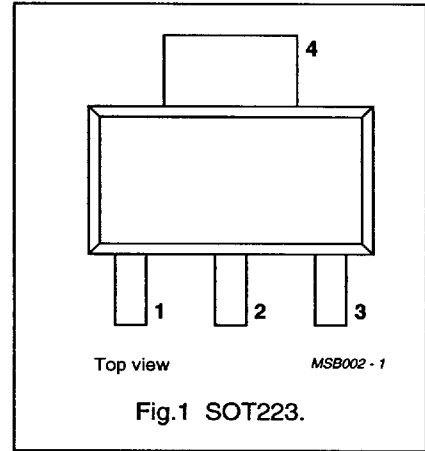
Intended for applications in the GHz range such as MATV or CATV amplifiers and RF communications subscriber equipment.

DESCRIPTION

NPN silicon planar epitaxial transistor in a plastic, 4-pin SOT223 package.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	emitter
4	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	–	15	V
I_C	collector current (DC)		–	–	200	mA
P_{tot}	total power dissipation	up to $T_s = 80\text{ }^\circ\text{C}$; note 1	–	–	2	W
h_{FE}	DC current gain	$I_C = 70\text{ mA}$; $V_{CE} = 8\text{ V}$	60	90	250	
C_{re}	feedback capacitance	$I_C = I_c = 0$; $V_{CE} = 12\text{ V}$; $f = 1\text{ MHz}$	–	0.7	–	pF
f_T	transition frequency	$I_C = 70\text{ mA}$; $V_{CE} = 12\text{ V}$; $f = 1\text{ GHz}$	–	7	–	GHz
G_{UM}	maximum unilateral power gain	$I_C = 70\text{ mA}$; $V_{CE} = 12\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ }^\circ\text{C}$	–	13	–	dB
$ S_{21} ^2$	insertion power gain	$I_C = 70\text{ mA}$; $V_{CE} = 12\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ }^\circ\text{C}$	–	12	–	dB

Note

1. T_s is the temperature at the soldering point of the collector pin.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	20	V
V _{CEO}	collector-emitter voltage	open base	–	15	V
V _{EBO}	emitter-base voltage	open collector	–	3	V
I _C	collector current (DC)		–	200	mA
P _{tot}	total power dissipation	up to T _s = 80 °C; note 1	–	2	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-s}	thermal resistance from junction to soldering point	note 1	35	K/W

Note to the Limiting values and Thermal characteristics

1. T_s is the temperature at the soldering point of the collector pin.

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CHARACTERISTICS

 $T_j = 25\text{ °C}$ (unless otherwise specified).

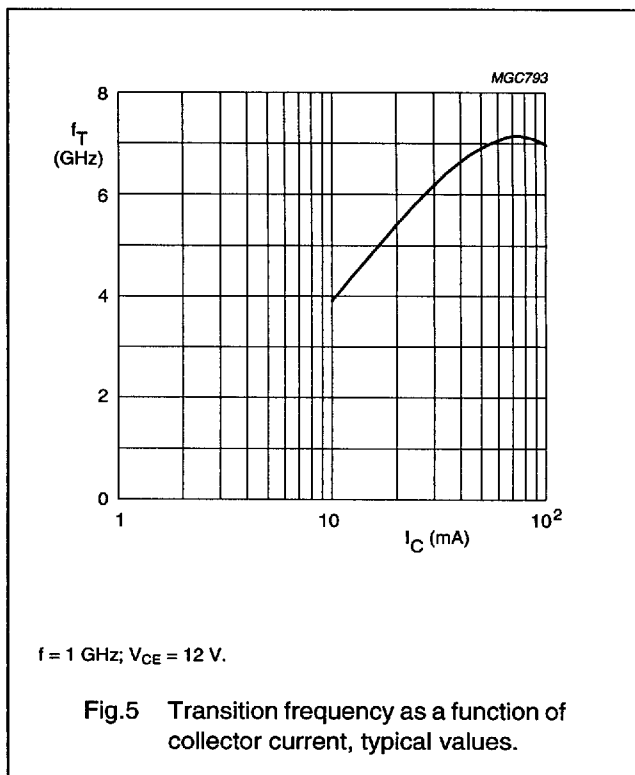
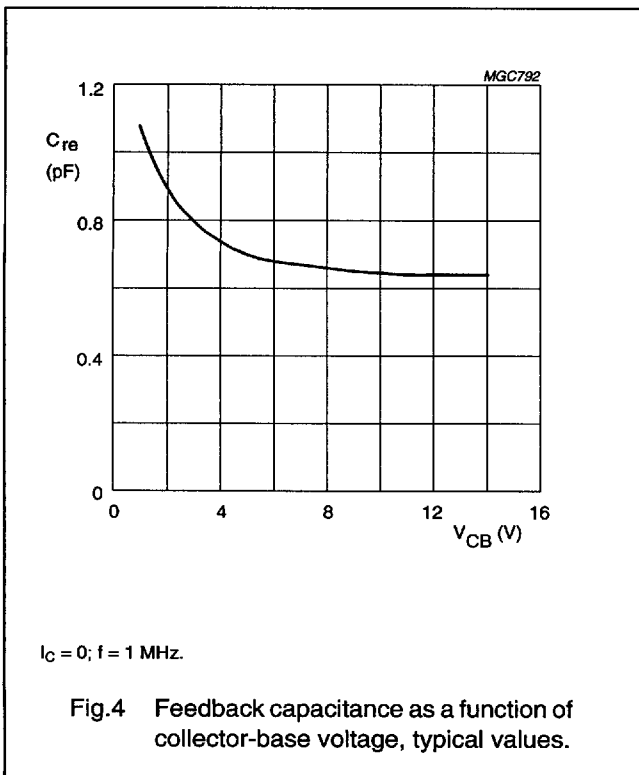
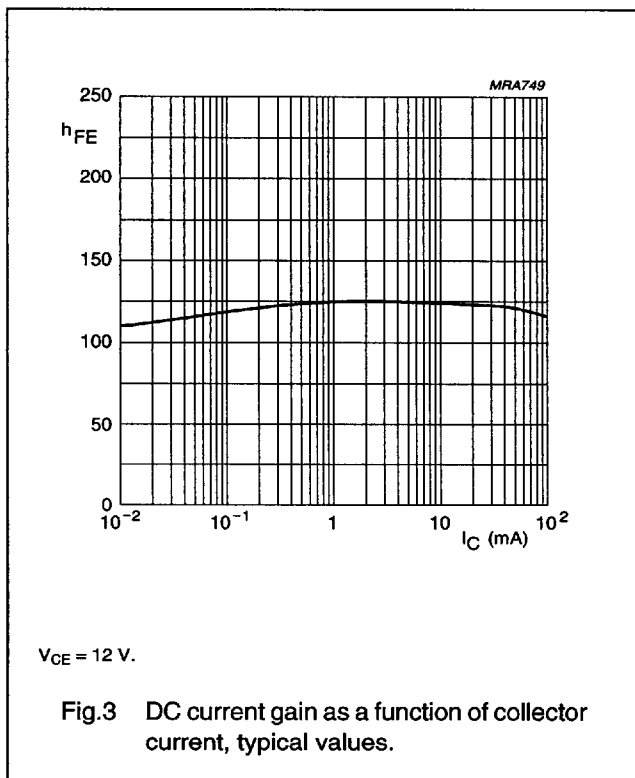
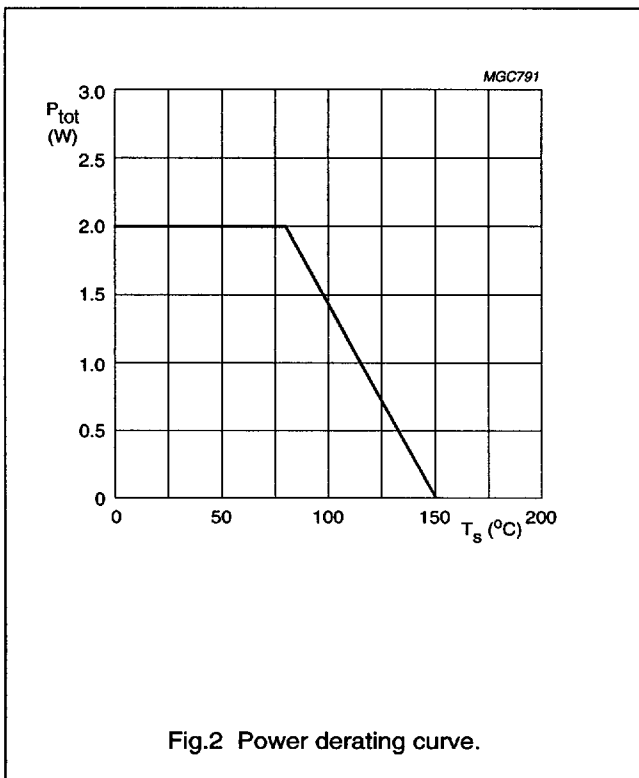
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 0.1\text{ mA}; I_E = 0$	–	–	20	V
$V_{(BR)CES}$	collector-emitter breakdown voltage	$I_C = 10\text{ mA}; I_B = 0$	–	–	15	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = 0.1\text{ mA}; I_C = 0$	–	–	3	V
I_{CBO}	collector-base leakage current	$I_E = 0; V_{CB} = 10\text{ V}$	–	–	100	nA
h_{FE}	DC current gain	$I_C = 70\text{ mA}; V_{CE} = 8\text{ V}$	60	90	250	
C_{re}	feedback capacitance	$I_B = I_b = 0; V_{CE} = 12\text{ V};$ $f = 1\text{ MHz}$	–	0.7	–	pF
f_T	transition frequency	$I_C = 70\text{ mA}; V_{CE} = 12\text{ V};$ $f = 1\text{ GHz}$	–	7	–	GHz
G_{UM}	maximum unilateral power gain; note 1	$I_C = 70\text{ mA}; V_{CE} = 12\text{ V};$ $f = 900\text{ MHz}; T_{amb} = 25\text{ °C}$	–	13	–	dB
		$I_C = 70\text{ mA}; V_{CE} = 12\text{ V};$ $f = 2\text{ GHz}; T_{amb} = 25\text{ °C}$	–	7.5	–	dB
$ S_{21} ^2$	insertion power gain	$I_C = 70\text{ mA}; V_{CE} = 12\text{ V};$ $f = 1\text{ GHz}; T_{amb} = 25\text{ °C}$	–	12	–	dB
V_o	output voltage	note 2	–	700	–	mV

Notes

- G_{UM} is the maximum unilateral power gain, assuming s_{12} is zero. $G_{UM} = 10 \log \frac{|s_{21}|^2}{(1 - |s_{11}|^2)(1 - |s_{22}|^2)}$ dB.
- $d_{im} = 60\text{ dB}$ (DIN45004B);
 $V_p = V_o; V_q = V_o - 6\text{ dB}; V_r = V_o - 6\text{ dB};$
 $f_p = 795.25\text{ MHz}; f_q = 803.25\text{ MHz}; f_r = 803.25\text{ MHz};$ measured at $f_{(p+q-r)} = 793.25\text{ MHz}$.

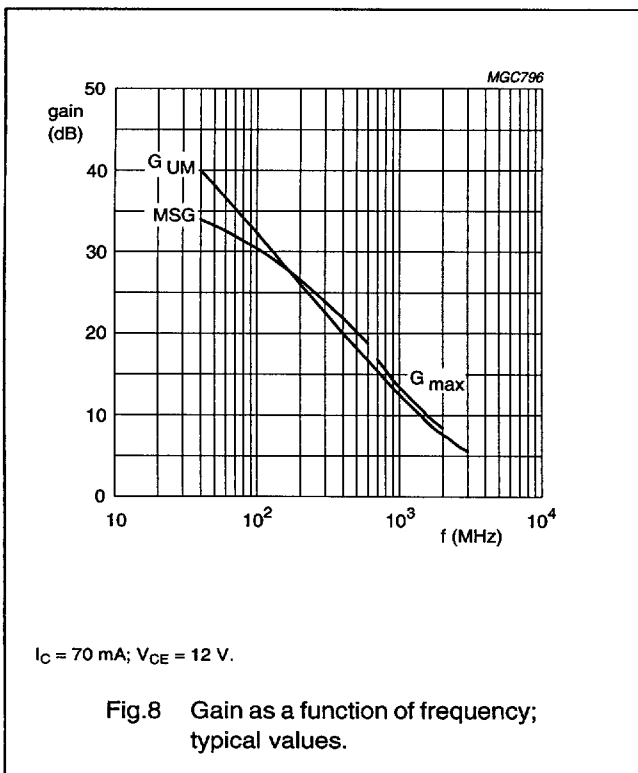
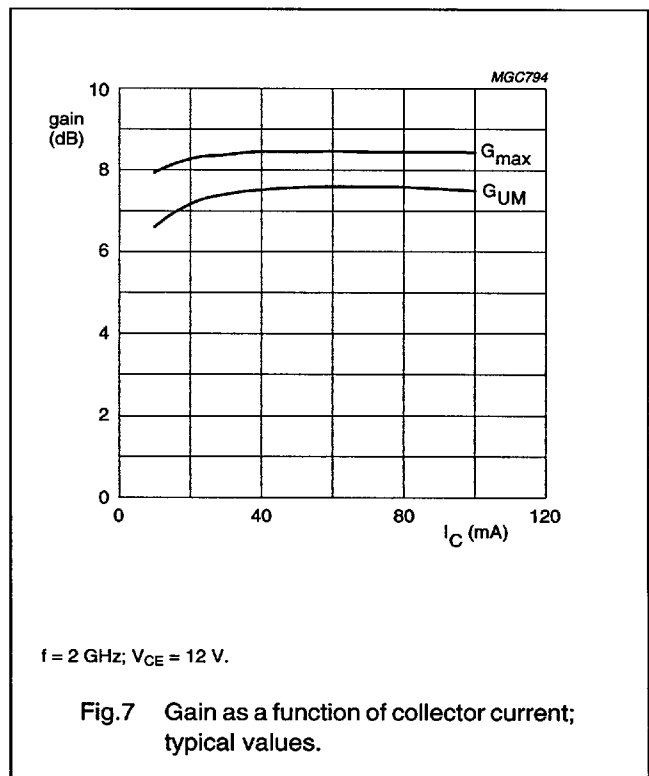
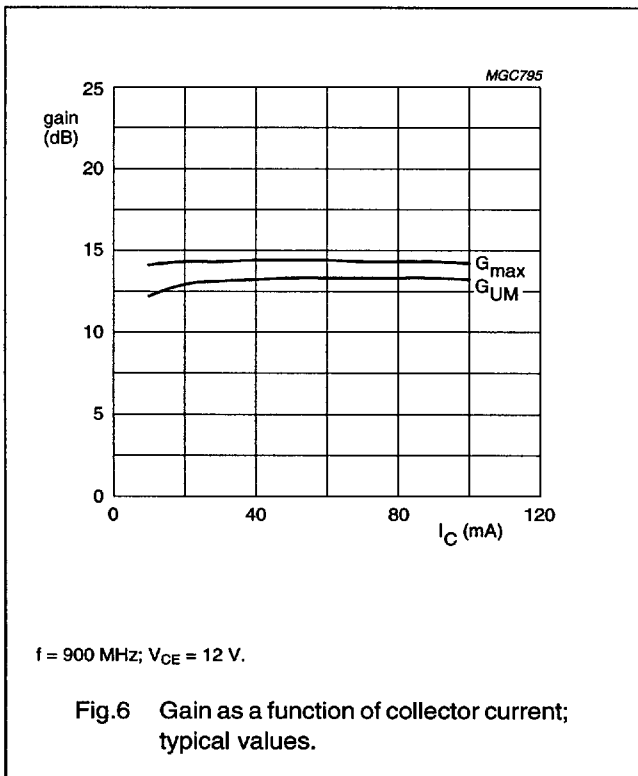
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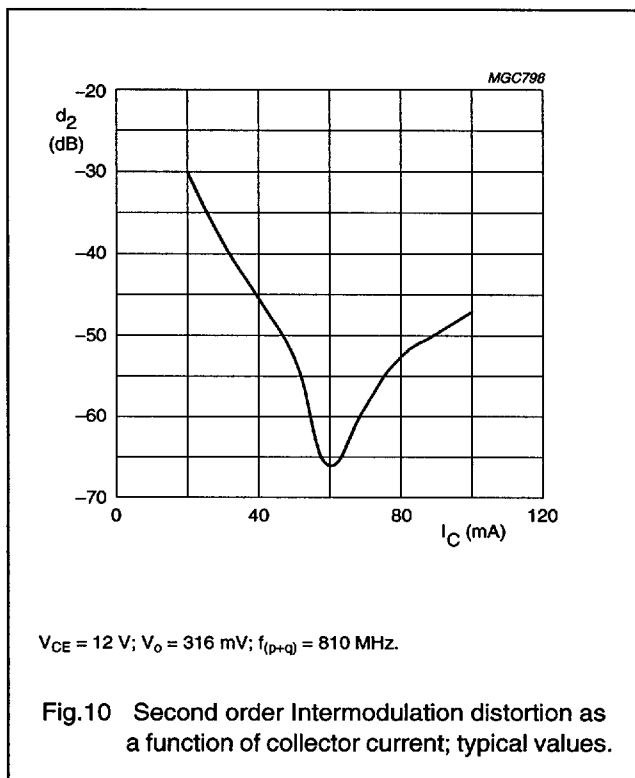
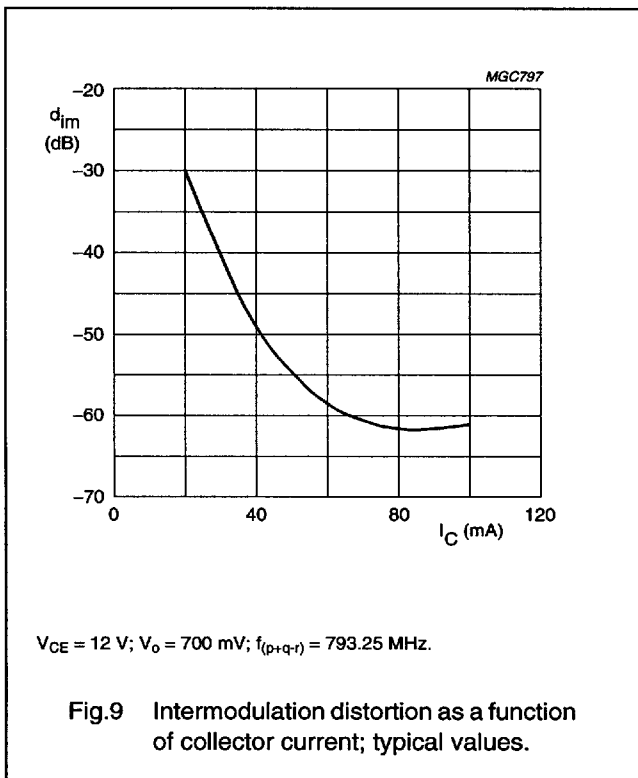
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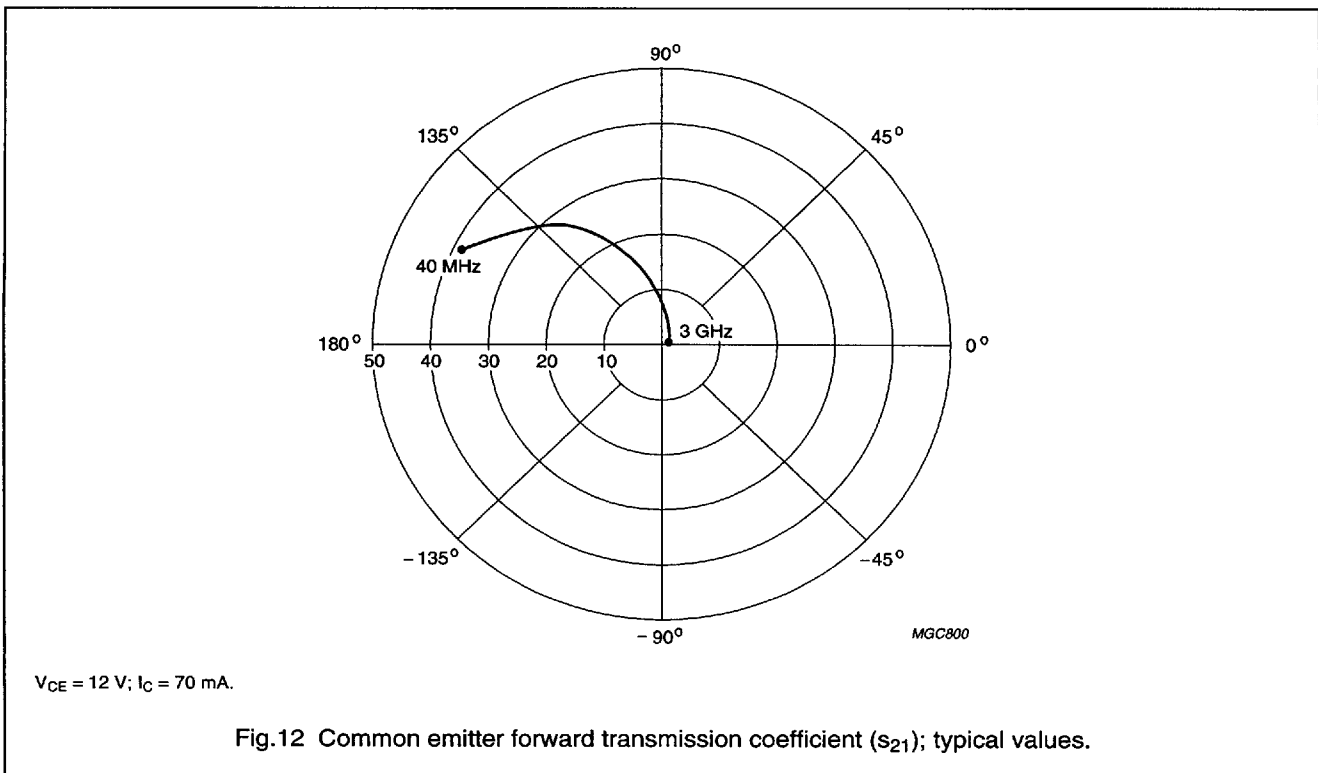
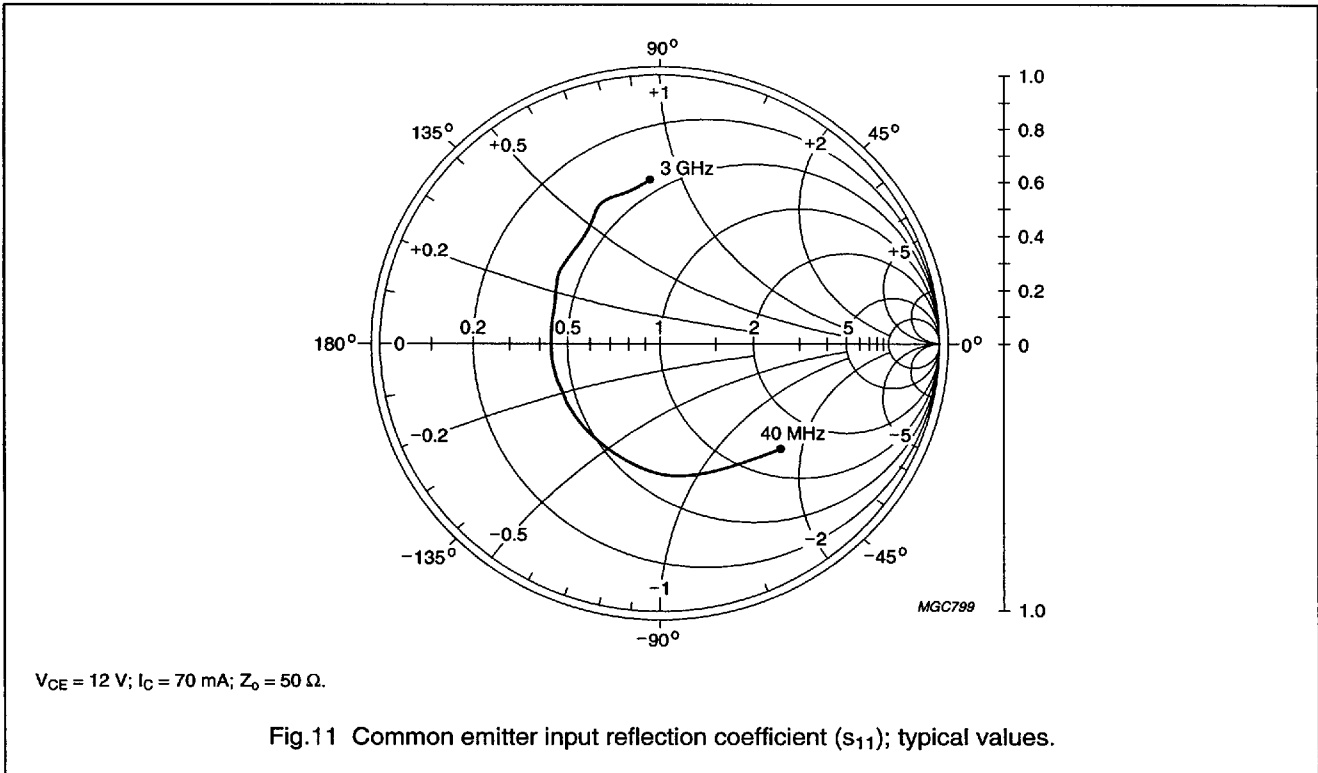
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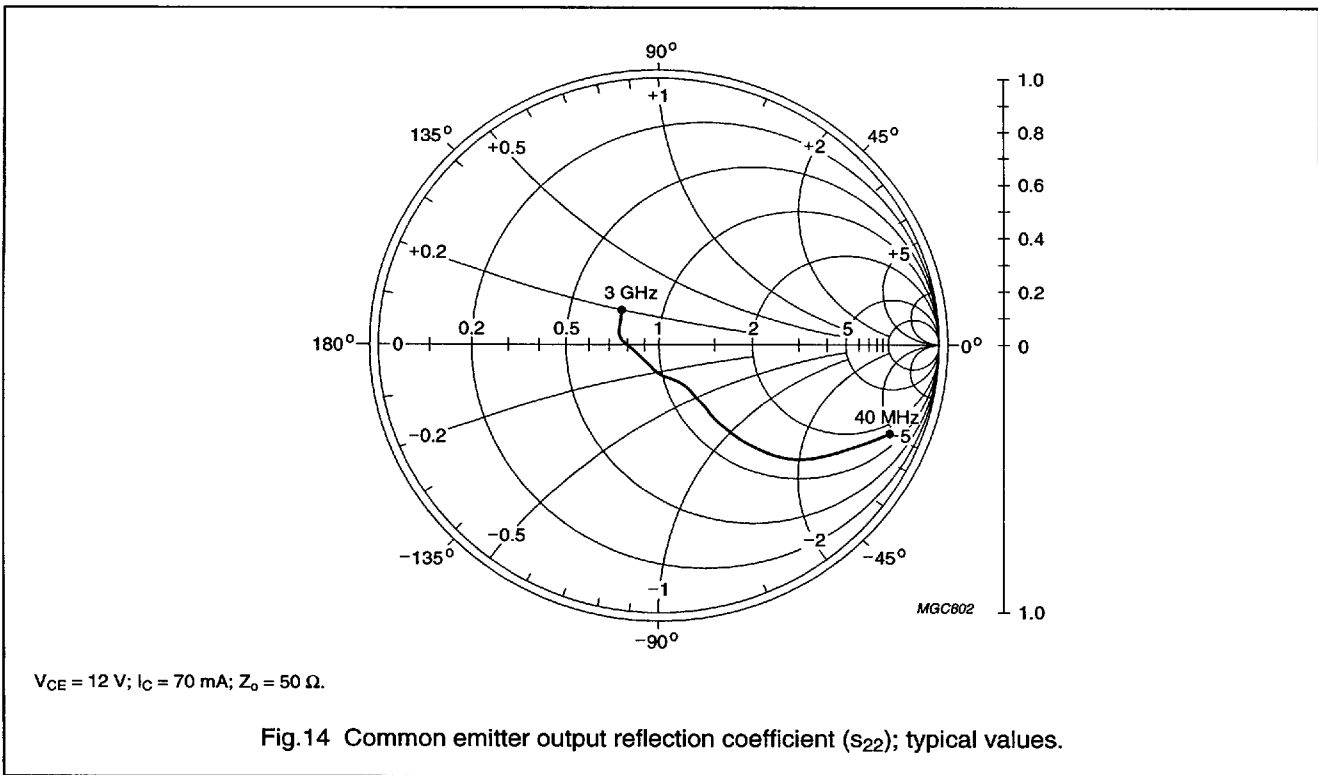
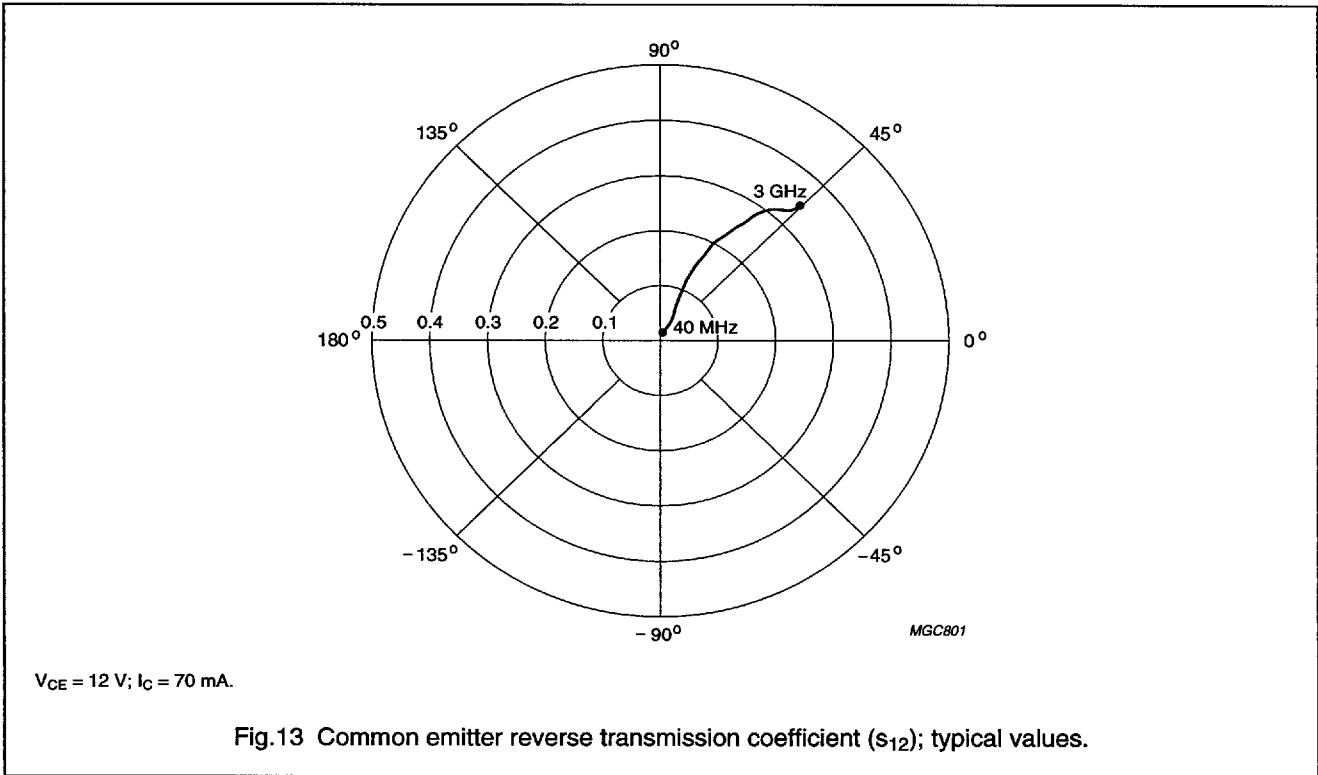
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SPICE parameters for the BFG591 crystal

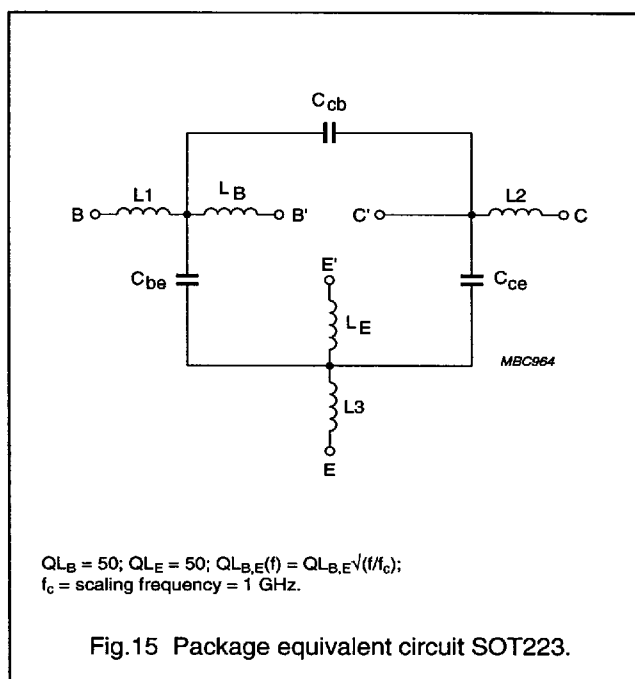
SEQUENCE No.	PARAMETER	VALUE	UNIT
1	IS	1.341	fA
2	BF	123.5	–
3	NF	.988	m
4	VAF	75.85	V
5	IKF	9.656	A
6	ISE	232.2	fA
7	NE	2.134	–
8	BR	10.22	–
9	NR	1.016	–
10	VAR	1.992	V
11	IKR	294.1	mA
12	ISC	211.0	aA
13	NC	997.2	–
14	RB	5.00	Ω
15	IRB	1.000	μ A
16	RBM	5.00	Ω
17	RE	1.275	Ω
18	RC	920.6	m Ω
19 (1)	XTB	0.000	–
20 (1)	EG	1.110	EV
21 (1)	XTI	3.000	–
22	CJE	3.821	pF
23	VJE	600.0	mV
24	MJE	348.5	m
25	TF	13.60	ps
26	XTF	71.73	–
27	VTF	10.28	V
28	ITF	1.929	A
29	PTF	0.000	deg
30	CJC	1.409	pF
31	VJC	219.4	mV
32	MJC	166.5	m
33	XCJ	2.340	m
34	TR	543.7	ns
35 (1)	CJS	0.000	F
36 (1)	VJS	750.0	mV
37 (1)	MJS	0.000	–
38	FC	733.2	m

Note

- These parameters have not been extracted, the default values are shown.

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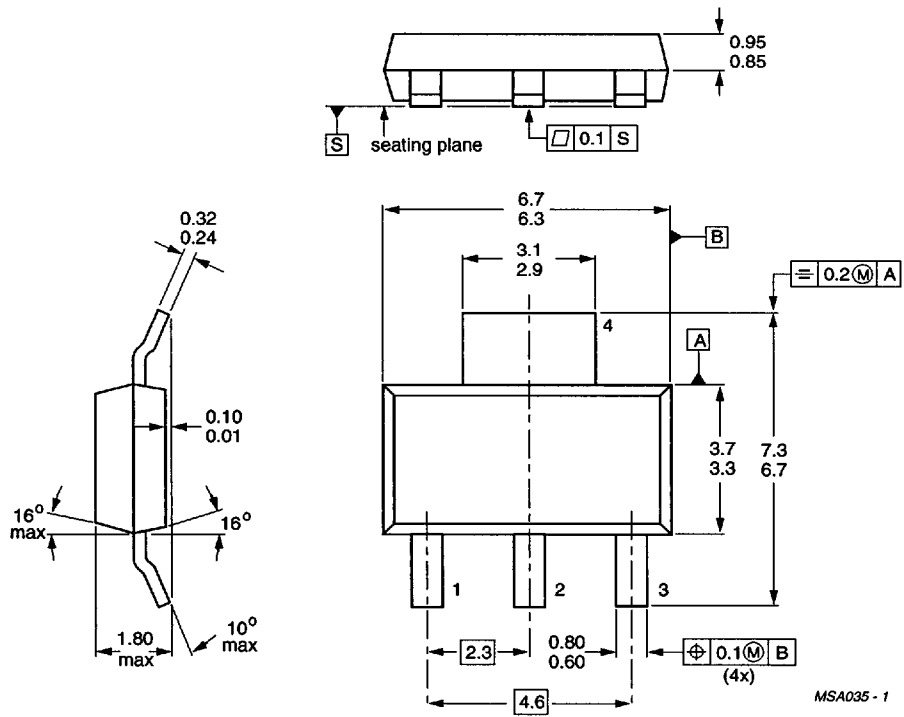
List of components (see Fig.15)

DESIGNATION	VALUE	UNIT
C_{be}	182	fF
C_{cb}	16	fF
C_{ce}	249	fF
L1	0.025	nH
L2	1.19	nH
L3	0.60	nH
L_B	1.50	nH
L_E	0.50	nH

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PACKAGE OUTLINE



Dimensions in mm.

Fig.16 SOT223.